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## AmberWave, RIT gain NSF grant

By Mark LaPedus

AmberWave Systems Inc. and the Rochester Institute of Technology (RIT) have been awarded a three-year research grant from the National Science Foundation (NSF).

The research grant will allow the two organizations to explore the integration of compound semiconductor devices on silicon using a technique called Aspect Ratio Trapping (ART).

Developed by AmberWave Systems, ART could allow manufacturers to combine different materials onto a silicon base, forming chips that use light pulses to carry data, similar to fiber optic technology. The result is increased speed of data transmission much faster than today's current systems allow.